

# EE Notes

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April 14, 2024

# Contents

- 1.1 Charge Carriers and Doping . . . . . 3
  - 1.1.1 Sources . . . . . 3
- 1.2 Doping and Drift . . . . . 4
  - 1.2.1 Sources . . . . . 4
- 1.3 EE105 04/09/2024 Lecture: Back-gate effect . . . . . 5

## 1.1 Charge Carriers and Doping

Doping is one method that we use in semiconductor devices

### 1.1.1 Sources

- [Razavi Electronics 1, Lec 1, Intro., Charge Carriers, Doping](#)

## **1.2 Doping and Drift**

### **1.2.1 Sources**

- [Razavi Electronics 1, Lec 2. Doping, Drift](#)

## 1.3 EE105 04/09/2024 Lecture: Back-gate effect

The source and drain in a MOSFET are symmetric. For the most part, we haven't worried about the body electrode up until this point